



ALPHA & OMEGA
SEMICONDUCTOR

AO4708

N-Channel Enhancement Mode Field Effect Transistor

SRFET™



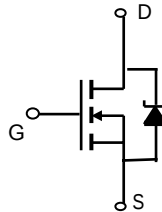
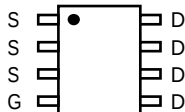
General Description

SRFET™ AO4708 uses advanced trench technology with a monolithically integrated Schottky diode to provide excellent $R_{DS(ON)}$ and low gate charge. This device is suitable for use as a low side FET in SMPS, load switching and general purpose applications. *Standard Product AO4708 is Pb-free (meets ROHS & Sony 259 specifications). AO4708L is a Green Product ordering option. AO4708L and AO4708 are electrically identical.*

Features

V_{DS} (V) = 30V
 I_D = 15A (V_{GS} = 10V)
 $R_{DS(ON)} < 8.7m\Omega$ (V_{GS} = 10V)
 $R_{DS(ON)} < 10.5m\Omega$ (V_{GS} = 4.5V)

UIS TESTED!
Rg, Ciss, Coss, Crss Tested



SRFET™
Soft Recovery MOSFET:
Integrated Schottky Diode

Absolute Maximum Ratings $T_A=25^\circ\text{C}$ unless otherwise noted

Parameter	Symbol	Maximum	Units
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	± 12	V
Continuous Drain Current ^A	I_{DSM}	15	A
$T_A=25^\circ\text{C}$			
$T_A=70^\circ\text{C}$		12	
Pulsed Drain Current ^B	I_{DM}	80	A
Avalanche Current ^B	I_{AR}	25	A
Repetitive avalanche energy $L=0.3mH$ ^B	E_{AR}	94	mJ
Power Dissipation ^A	P_{DSM}	3.1	W
$T_A=25^\circ\text{C}$			
$T_A=70^\circ\text{C}$		2.0	
Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 150	$^\circ\text{C}$

Thermal Characteristics

Parameter	Symbol	Typ	Max	Units
Maximum Junction-to-Ambient ^A	$R_{\theta JA}$	32	40	$^\circ\text{C/W}$
$t \leq 10s$				
Maximum Junction-to-Ambient ^A	$R_{\theta JA}$	60	75	$^\circ\text{C/W}$
Steady-State				
Maximum Junction-to-Lead ^C	$R_{\theta JL}$	17	24	$^\circ\text{C/W}$
Steady-State				

Electrical Characteristics ($T_J=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV_{DSS}	Drain-Source Breakdown Voltage	$I_D=250\mu\text{A}$, $V_{GS}=0\text{V}$	30			V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=24\text{V}$, $V_{GS}=0\text{V}$ $T_J=125^\circ\text{C}$			0.1 20	mA
I_{GSS}	Gate-Body leakage current	$V_{DS}=0\text{V}$, $V_{GS}=\pm 12\text{V}$			0.1	μA
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}$, $I_D=250\mu\text{A}$	1.4	1.8	2.4	V
$I_{D(ON)}$	On state drain current	$V_{GS}=4.5\text{V}$, $V_{DS}=5\text{V}$	80			A
$R_{DS(ON)}$	Static Drain-Source On-Resistance	$V_{GS}=10\text{V}$, $I_D=15\text{A}$ $T_J=125^\circ\text{C}$		7.2 10.5	8.7 13.1	$\text{m}\Omega$
		$V_{GS}=4.5\text{V}$, $I_D=14\text{A}$		8.6	10.5	$\text{m}\Omega$
g_{FS}	Forward Transconductance	$V_{DS}=5\text{V}$, $I_D=15\text{A}$		85		S
V_{SD}	Diode Forward Voltage	$I_S=1\text{A}$, $V_{GS}=0\text{V}$		0.39	0.5	V
I_S	Maximum Body-Diode + Schottky Continuous Current				5.5	A
DYNAMIC PARAMETERS						
C_{iss}	Input Capacitance	$V_{GS}=0\text{V}$, $V_{DS}=15\text{V}$, $f=1\text{MHz}$		2800	3360	pF
C_{oss}	Output Capacitance			390		pF
C_{rss}	Reverse Transfer Capacitance			145		pF
R_g	Gate resistance	$V_{GS}=0\text{V}$, $V_{DS}=0\text{V}$, $f=1\text{MHz}$		0.8	1.5	Ω
SWITCHING PARAMETERS						
$Q_g(10\text{V})$	Total Gate Charge	$V_{GS}=10\text{V}$, $V_{DS}=15\text{V}$, $I_D=15\text{A}$		42	52	nC
$Q_g(4.5\text{V})$	Total Gate Charge			19		nC
Q_{gs}	Gate Source Charge			7		nC
Q_{gd}	Gate Drain Charge			6		nC
$t_{D(on)}$	Turn-On DelayTime	$V_{GS}=10\text{V}$, $V_{DS}=15\text{V}$, $R_L=1\Omega$, $R_{GEN}=3\Omega$		7		ns
t_r	Turn-On Rise Time			7		ns
$t_{D(off)}$	Turn-Off DelayTime			31		ns
t_f	Turn-Off Fall Time			5		ns
t_{rr}	Body Diode Reverse Recovery Time	$I_F=15\text{A}$, $dI/dt=300\text{A}/\mu\text{s}$		13	15	ns
Q_{rr}	Body Diode Reverse Recovery Charge	$I_F=15\text{A}$, $dI/dt=300\text{A}/\mu\text{s}$		12		nC

A: The value of $R_{\theta JA}$ is measured with the device in a still air environment with $T_A=25^\circ\text{C}$. The power dissipation P_{DSM} and current rating I_{DSM} are based on $T_{J(MAX)}=150^\circ\text{C}$, using $t \leq 10\text{s}$ junction-to-ambient thermal resistance.

B: Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)}=150^\circ\text{C}$.

C: The $R_{\theta JA}$ is the sum of the thermal impedance from junction to lead $R_{\theta JL}$ and lead to ambient.

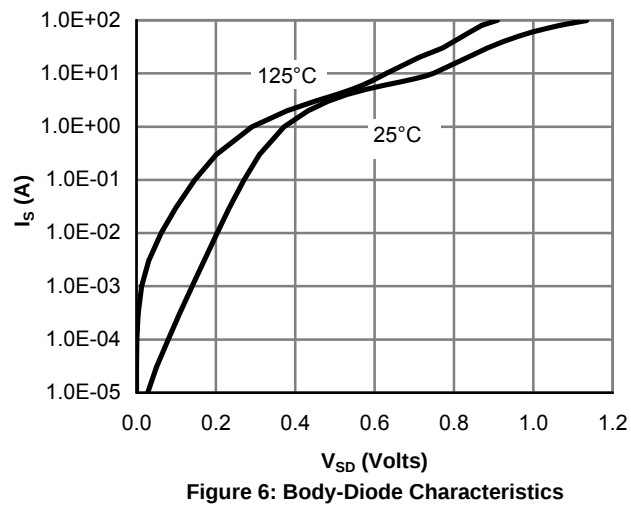
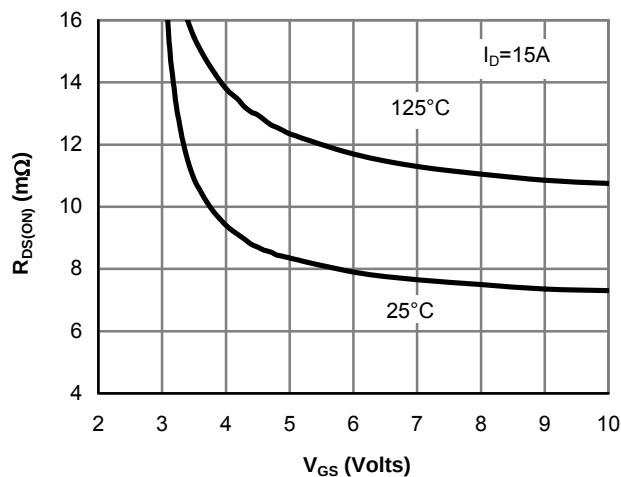
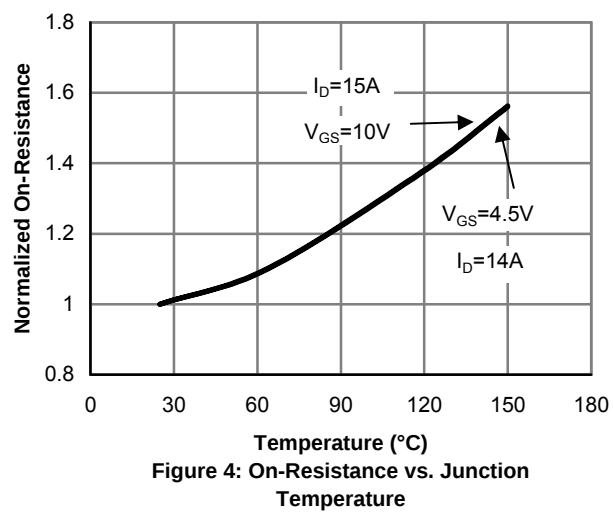
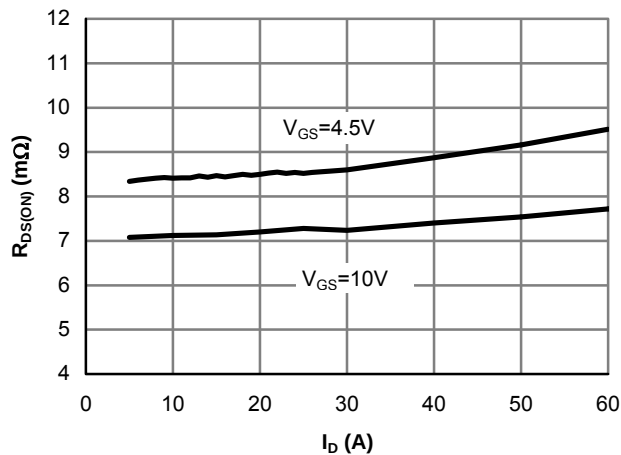
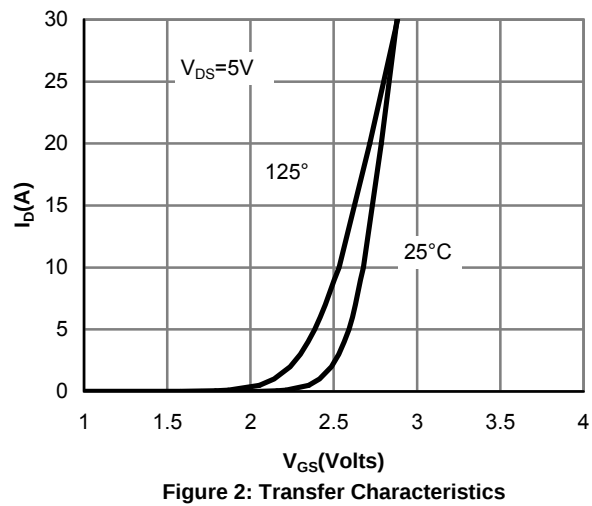
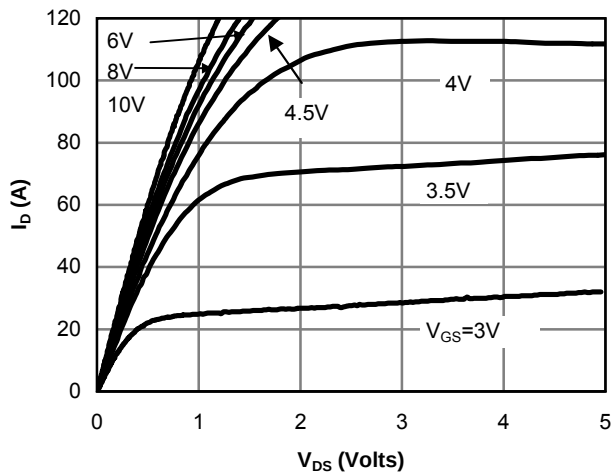
D: The static characteristics in Figures 1 to 6 are obtained using $<300\mu\text{s}$ pulses, duty cycle 0.5% max.

E: These tests are performed with the device mounted on 1 in 2 FR-4 board with 2oz. Copper, in a still air environment with $T_A=25^\circ\text{C}$. The SOA curve provides a single pulse rating.

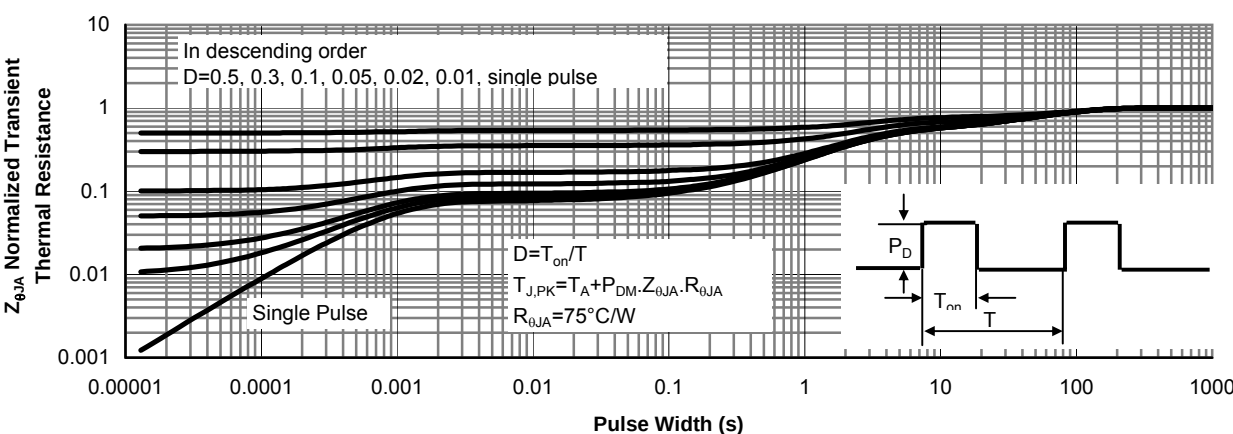
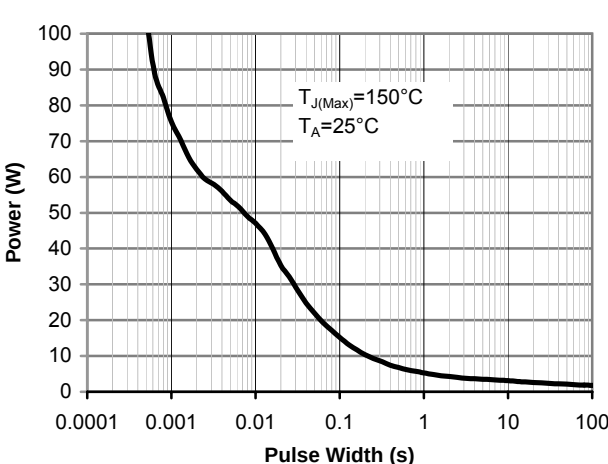
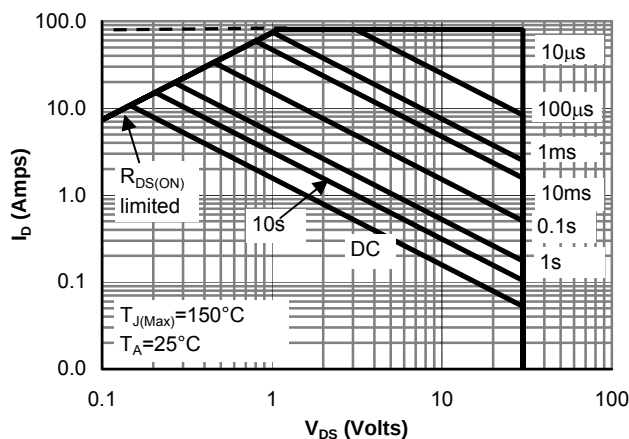
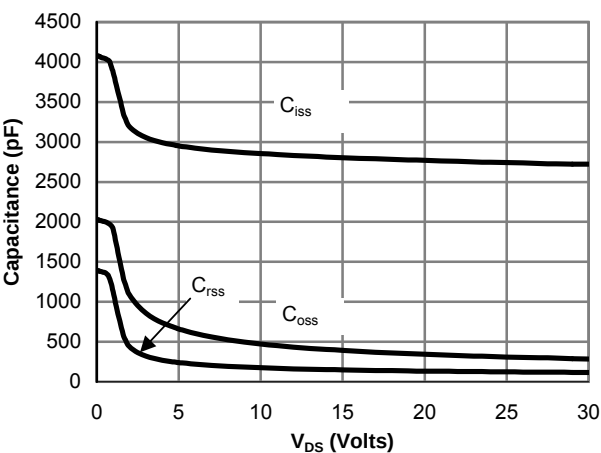
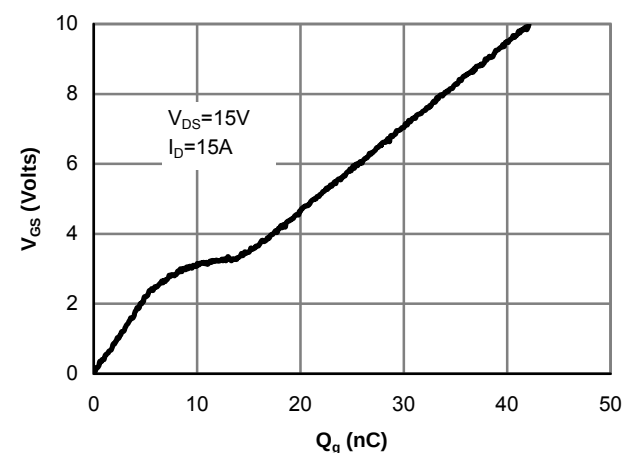
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TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS



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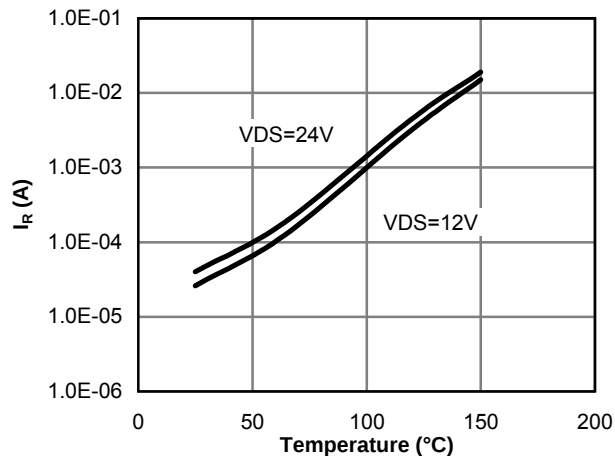


Figure 12: Diode Reverse Leakage Current vs. Junction Temperature

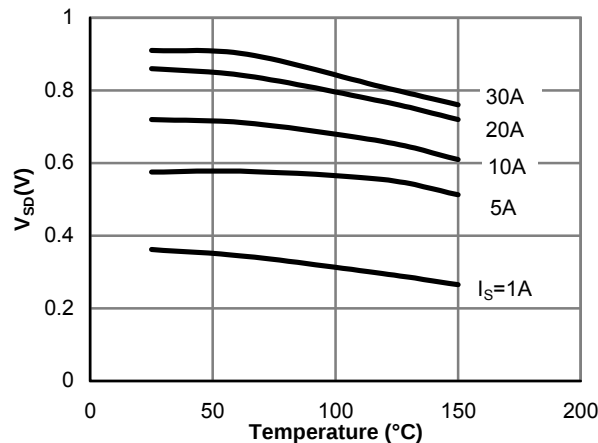


Figure 13: Diode Forward voltage vs. Junction Temperature

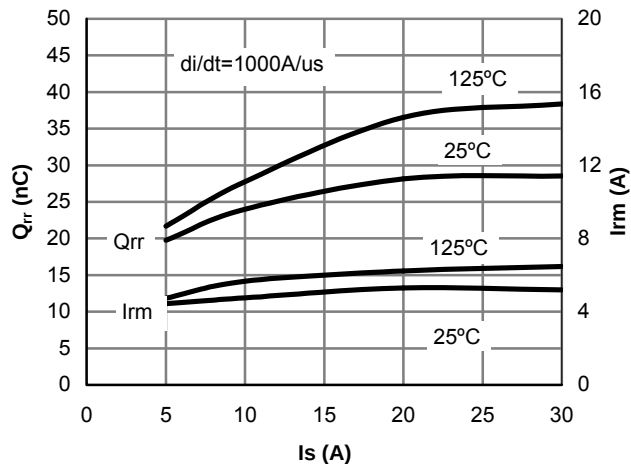


Figure 14: Diode Reverse Recovery Charge and Peak Current vs. Conduction Current

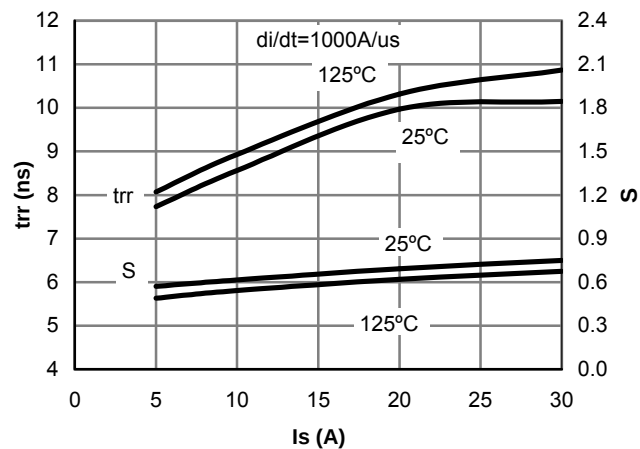


Figure 15: Diode Reverse Recovery Time and Soft Coefficient vs. Conduction Current

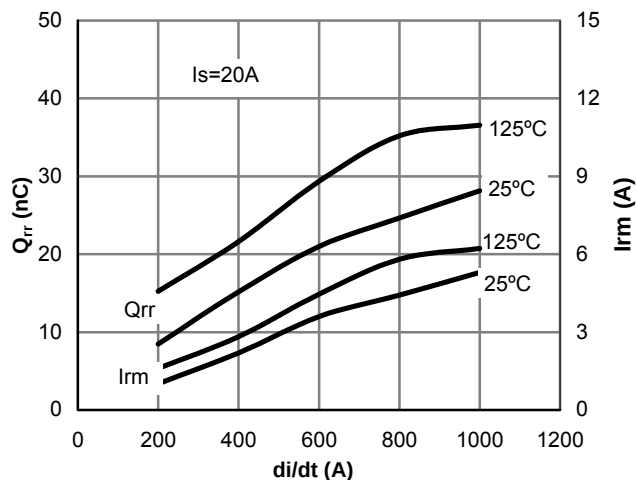


Figure 16: Diode Reverse Recovery Charge and Peak Current vs. di/dt

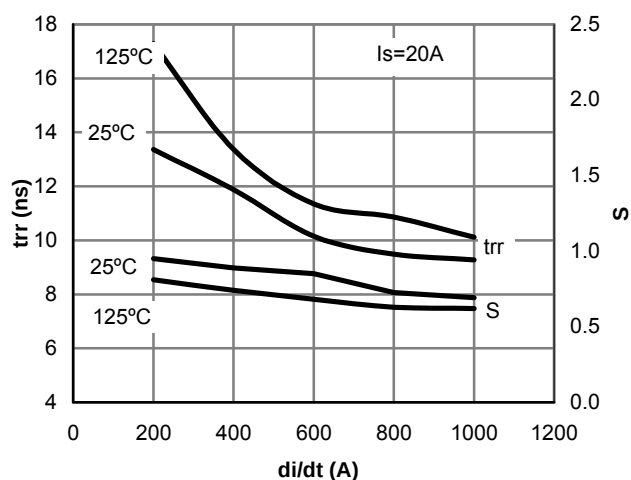


Figure 17: Diode Reverse Recovery Time and Soft Coefficient vs. di/dt